

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1845	(memory and (ONO (\$2oxide with nitride)) and (float\$4 ((charge electron) near2 (stor\$4 keep\$4 hold\$4))) and control\$3).dm.	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:32
L2	445	1 and ((high\$3 great\$3) near3 (dielectric k))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:34
L3	138	1 and ((high\$3 great\$3) near3 (dielectric k)).dm.	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:34
L4	43	3 and (metal\$4 near2 (\$2oxide))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:35
L5	1	10/ 189643	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:37
L6	1	5 and barrier	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:37
L7	1	6 and \$4oxide	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:39
L8	27	4 and ONO	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:46
L9	9	("20020072177" "5904523" "6143607" "6248633" "6384448" "6525970" "6559007" "6610614").FN. OR ("6828623").URPN.	US-PGRUB; USPAT; USOCR	OR	OFF	2008/04/07 18:56
L10	24	2 and adjoin\$3	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:57

L11	18	10 not 8	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 18:57
L12	3073	257/315.ccls.	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:00
L13	1813	257/314.ccls.	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:01
L14	1306	257/321.ccls.	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:01
L15	10857	memory and (substrate wafer carrier board) with ((silicon adj \$2oxide) "SiO. sub.2" "SiO") and (float\$4 ((charge electron) near2 (stor\$4 keep\$4 hold\$4)) and ((high\$3 great\$3) near3 (dielectric k))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:15
L16	8037	15 and (@ad< "20030909" @riac< "20030909")	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:17
L17	2606	16 and (metal\$4 near2 (\$2oxide))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:17
L18	1951	17 and (ONO (\$2oxide with nitride))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:17
L19	451	17 and ((ONO (\$2oxide with nitride)) with (float\$4 ((charge electron) near2 (stor\$4 keep\$4 hold\$4))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:18
L20	322	19 and (control\$3) with (float\$4 ((charge electron) near2 (stor\$4 keep\$4 hold\$4))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:19
L21	322	19 and (control\$3 with (float\$4 ((charge electron) near2 (stor\$4 keep\$4 hold\$4))))	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:19

L22	309	21 and source and drain	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:20
L23	213	22 and "ONO"	US-PGRUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2008/04/07 19:20
S1	11	FASTOW-RICHARD-M.IN.	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:29
S2	36	he-yue-song.in.	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:29
S3	43	wang-zhigang.in.	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:29
S4	81	S1 S2 S3	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:29
S5	12	S4 and (source and drain and gate and ((high adj k) or (high adj dielectric adj constant)))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:30
S6	12	S5 and ((silicon adj dioxide) or "SiO.sub.2")	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:37
S7	193	(flash adj memory) and (((high adj k) or (high near2 constant)) with dielectric) and ((silicon adj dioxide) or "SiO.sub.2") and (nitrit\$4 or oxynitr\$4)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:39
S8	183	S7 not S4	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:40
S9	96	S8 and (substrate and (float\$4 adj gate))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:40
S10	68	S9 and ((high-k or (high adj k) or (high adj dielectric adj constant)) with material)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:42
S11	67	S10 and ("ONO" or (oxide and nitride))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2006/04/25 10:54
S12	38	S10 and ("ONO")	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:43
S13	38	S12 and (control44 or gate)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:43
S14	32	S12 and (control\$4 adj gate)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/18 20:43
S15	9	"6143606"	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 11:59

S16	1	S15 and (thin adj gate adj oxide)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:09
S17	1	S16 and oxide	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:10
S18	11	((US-20040191988-\$ or US-20040159880-\$).did. or (US-6617639-\$ or US-6803275-\$ or US-6803272-\$ or US-6750502-\$ or US-6713810-\$ or US-6693321-\$ or US-6642573-\$ or US-6849489-\$ or US-6143606-\$).did.	US-PGRUB; USPAT	OR	ON	2005/03/19 12:13
S19	9	S18 and ("ONO" or ONO) and (high adj k or (high-k) or (high adj dielectric adj constant))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:14
S20	9	S19 and float\$4	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:18
S21	151	(FLASH adj memory) and "ONO" and float \$4 and (oxide with ((high adj k) or (high-k) or (high adj dielectric adj constant)))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:26
S22	142	S21 not (S15 S16 S17 S18 S19 S20)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:27
S23	6	S22 and ((gate adj oxide) with ((high adj k) or (high-k) or (high adj dielectric adj constant)))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:29
S24	8	substrate and "ONO" and float\$4 and ((gate adj oxide) with ((high adj k) or (high-k) or (high adj dielectric adj constant)))	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:27
S25	136	S21 not (S15 S16 S17 S18 S19 S20 S23)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:27
S26	2	S24 not (S15 S16 S17 S18 S19 S20 S23)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:27
S27	8	(gate adj oxide) with ((high adj k) or (high-k) or (high adj dielectric adj constant)) and ("ONO" and float\$4)	US-PGRUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2005/03/19 12:30
S28	10	((US-20040159880-\$).did. or (US-6143606-\$ or US-6617639-\$ or US-6642573-\$ or US-6693321-\$ or US-6713810-\$ or US-6750502-\$ or US-6803272-\$ or US-6803275-\$ or US-6849489-\$).did.	US-PGRUB; USPAT	OR	ON	2005/08/09 19:10
S29	10	S28 and ("ONO" or (silicon adj (\$3oxide or nitride)))	US-PGRUB; USPAT	OR	ON	2005/08/09 19:11
S30	3	((("5708285") or ("5491657") or ("6091633")).PN.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/08/10 14:06
S31	1	(gate near2 (stack or structure) and "ONO").ti.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 14:37

S32	59	(gate near2 (stack or structure) and "ONO").ab.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:51
S33	2	S32 and ((dielectric or insulat\$4) with (high adj ("k" or constant)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:30
S34	2	S32 and ((dielectric or insulat\$4) with (high adj2 ("k" or constant)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:30
S35	21	S32 and (float\$4 and control)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:46
S36	36	S32 not (S33 S34 S35)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:46
S37	86	(gate near2 (stack or structure) same "ONO") and (float\$4 and control) and (high adj2 ("k" or constant)) and substrate	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 17:13
S38	86	S37 not S32	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:53
S39	80	S38 and (source and drain)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 15:53
S40	41	("20030042527" "20030042532" "20030043622" "20030043630" "20030043632" "20030043633" "20030043637" "20030045082" "20030048666" "20040004245" "20040004247" "20040004859" "3978577" "4412902" "4449205" "4495219" "4717943" "4780424" "4794565" "4870470" "5350738" "5445984" "5455792" "5510278" "5617351" "5646430" "5691230" "5801401" "5852306" "5936274" "5952692" "5981350" "6025627" "6031263" "6101131" "6127227" "6134175" "6143636" "6169306" "6208164" "6288419").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2005/08/10 17:10
S41	42	(gate near2 (stack or structure)) and (second adj2 "ONO") and (float\$4 and control)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 17:14
S42	42	S41 not (S33 S34 S35 S39)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/08/10 17:15

S43	1	("6596554").PN.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/08/10 19:06
S44	41	("20030042527" "20030042532" "20030043622" "20030043630" "20030043632" "20030043633" "20030043637" "20030045082" "20030048666" "20040004245" "20040004247" "20040004859" "3978577" "4412902" "4449205" "4495219" "4717943" "4780424" "4794565" "4870470" "5350738" "5445984" "5455792" "5510278" "5617951" "5646430" "5691230" "5801401" "5852306" "5936274" "5952692" "5981350" "6025627" "6031263" "6101131" "6127227" "6134175" "6143636" "6169306" "6208164" "6288419").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2005/12/11 22:00
S45	6	S44 and "ONO"	US-PGRUB; USPAT; USOCR	OR	ON	2005/12/11 22:05
S46	121	((("ONO" or (\$oxide near4 nitride)) with ((gate or tunnel\$4 near2 (dielectric or insulat\$4 oxide))) and (float\$4 near3 (silicon or polysilicon))) and ((("ONO" or (oxide near4 nitride)) near3 (interpoly adj (insulat\$4 or dielectric or layer))) and substrate	US-PGRUB; USPAT; USOCR	OR	ON	2005/12/11 22:40
S47	22	S46 and (high adj ("k" or (dielectric adj constant)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/11 22:19
S48	97	(S46 not S47) and (@ad< "20030909" or @rlad< "20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 12:45
S49	217	((("ONO" or (\$oxide near4 nitride)) near4 ((gate or tunnel\$4 near2 (dielectric or insulat\$4 oxide))) and ((("ONO" or (oxide near4 nitride)) near3 (inter or (inter adj poly) or interpoly adj (insulat\$4 or dielectric or layer)))	US-PGRUB; USPAT; USOCR	OR	ON	2005/12/11 22:42
S50	135	S49 not (S44 S45 S46)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/11 22:43
S52	57	S50 and ((silicon or poly or polysilicon) near3 float\$4 near2 gate) and substrate	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/12/11 22:44
S53	55	S52 and (@ad< "20030909" or @rlad< "20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/25 10:52
S54	5548	257/52,310,314,321,524,e21.625,e21.639, e21.675,e21.681,e21.687,e21.688,e21.69. ccls.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 19:56

S55	1206	S54 and (float\$4 or trap\$4) and ("ONO" or (\$2oxide adj2 nitride adj2 \$2oxide\$2)) and control\$3	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 20:02
S56	1063	S55 and (@ad<"20030909" or @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 19:58
S57	996	S56 and source and drain and (\$5silicon)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 19:59
S58	106	S57 and (high adj ("k" or dielectric))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 20:00
S60	90	S58 and (\$5silicon with (float\$4 or trap \$4))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 20:01
S61	44	S60 and (control\$4 with ("ONO" or (\$2oxide adj2 nitride adj2 \$2oxide\$2)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 20:03
S62	58	("4142004" "4551231" "4623912" "4814292" "4872043" "5102832" "5112773" "5159430" "5264724" "5288527" "5352330" "5366917" "5385863" "5397720" "5445999" "5489542" "5707746" "5707898" "5711998" "5821603" "5880008" "5904860" "5936291" "5946542" "5972765" "5972804" "6013310" "6017784" "6017808" "6025281" "6048795" "6060954" "6087206" "6136641" "6143608" "6147014" "6150725" "6197701" "6204203" "6248673" "6251726" "6255230" "6258730" "6265327" "6274442" "6284583" "6316354" "6323519" "6348380" "6380014" "6387761" "6420752" "6465370" "6483172" "6485988" "6544908" "6551867" "6559007").FN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/04/24 20:14
S63	18	"6559007"	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/24 20:20
S72	18	"6559007"	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/04/25 11:43

S73	56	("4958321" "5077691" "5335198" "5407870" "5457336" "5470773" "5517443" "5561620" "5590076" "5596531" "5598369" "5617357" "5629893" "5652155" "5708588" "5768192" "5805502" "5844840" "5852582" "5856946" "5907781" "5909396" "5912489" "5933730" "5939763" "5966618" "5972751" "5981404" "5991202" "5999452" "6001689" "6001713" "6011725" "6017791" "6037235" "6063666" "6133605" "6143608" "6143612" "6159795" "6160317" "6166951" "6177322" "6188606" "6198664" "6207978" "6215148" "6245689" "6248628" "6252270" "6294430" "6348420" "6384448" "6395654" "6512264" "6559007" "9080639").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/04/25 11:52
S74	41	("20030042527" "20030042532" "20030043622" "20030043630" "20030043632" "20030043633" "20030043637" "20030045082" "20030048666" "20040004245" "20040004247" "20040004859" "3978577" "4412902" "4449205" "4495219" "4717943" "4780424" "4794565" "4870470" "5350738" "5445984" "5455792" "5510278" "5617351" "5646430" "5691230" "5801401" "5852306" "5936274" "5952692" "5981350" "6025627" "6031263" "6101131" "6127227" "6134175" "6143636" "6169306" "6208164" "6288419").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/04/25 12:02
S75	7317	257/52,260,314,315,316,321,e21.179, e21.18,e21.422,e21.423,e21.687,e29.129, e29.3.ccls.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:17
S76	2751	438/257,263.ccls.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:17
S77	819	H01L29/76.ipc.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:18
S78	3	H01L29/778.ipc.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:18
S79	767	H01L21/336.ipc.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 18:07
S80	10269	S75 S76 S77 S78 S79	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:19

S87	7518	S80 and ((float\$4 or ((charg\$4 or electron) with (trap\$4 hold\$4 keep\$3)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 16:57
S88	875	S87 and (high near2 (dielectric or "k"))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:41
S89	705	S88 and (\$4silicon with (float\$4 or ((charg\$4 or electrone) with (trap\$4 hold\$4 keep\$3))))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:24
S90	525	S89 and ("ONO" or (oxide adj2 nitride))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:32
S91	386	S90 and (@ad<"20030909" or @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 17:03
S92	353	S91 and ("SiO.sub.2" or (silicon adj \$2oxide)) and control\$3	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:25
S93	349	S92 and float\$3	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:26
S94	346	S92 and (float\$3 adj (gate layer film))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:30
S95	329	S94 and source and drain	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:30
S96	29	S95 and (control\$3 near3 ("ONO" or (oxide adj2 nitride)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:40
S97	300	S95 not S96	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/10 17:41
S98	57	S97 and ((high near2 (dielectric or "k")) with metal\$4)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 12:35

S99	57	(US-20060081941-\$ or US-20060008997-\$ or US-20060001049-\$ or US-20050169054-\$ or US-20050151184-\$ or US-20050026349-\$ or US-20050023602-\$ or US-20050023595-\$ or US-20040191988-\$ or US-20040190342-\$ or US-20040168145-\$ or US-20040164342-\$ or US-20040160830-\$ or US-20040070030-\$ or US-20040051134-\$ or US-20030151084-\$ or US-20030043637-\$ or US-20030043622-\$ or US-20030042532-\$ or US-20030042528-\$ or US-20030042527-\$).did. or (US-7068544-\$ or US-7042043-\$ or US-7027328-\$ or US-7012297-\$ or US-7001814-\$ or US-6969886-\$ or US-6963103-\$ or US-6958937-\$ or US-6952032-\$ or US-6924186-\$ or US-6903406-\$ or US-6887758-\$ or US-6858899-\$ or US-6803275-\$ or US-6803272-\$ or US-6794236-\$ or US-6778441-\$ or US-6754108-\$ or US-6753570-\$ or US-6750502-\$ or US-6750066-\$ or US-6740605-\$ or US-6713812-\$ or US-6706576-\$ or US-6689658-\$ or US-6674138-\$).did. or (US-6642573-\$ or US-6627945-\$ or US-6617639-\$ or US-6580118-\$ or US-6461905-\$ or US-6344403-\$ or US-6297095-\$ or US-5998264-\$ or US-5650648-\$ or US-5498558-\$).did.	US-PGRUB; USPAT	OR	ON	2006/07/11 12:35
S100	668	gate and (high adj2 ("k" or dielectric)) and \$2oxide and (polysilicon with (float\$4 or ((charg\$4 or electron) with (trap\$4 hold \$4 keep\$3)))) and ("ONC" or (\$3oxide with nitride)) and control\$4	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:58
S101	22	((US-20020117709-\$ or US-20050012141-\$ or US-20040264236-\$ or US-20030141536-\$ or US-20020145161-\$).did. or (US-6872972-\$ or US-6750502-\$ or US-6767791-\$ or US-6849489-\$ or US-5619052-\$ or US-6713810-\$ or US-6998675-\$ or US-6921937-\$ or US-6559007-\$ or US-6784480-\$ or US-6617639-\$ or US-6143606-\$ or US-6693321-\$ or US-6455890-\$ or US-6815805-\$ or US-7068544-\$).did. or (JP-09148460-\$).did.	US-PGRUB; USPAT; JPO	OR	ON	2006/07/11 12:45
S103	452	(S100 not (S99 S101)) and (@ad< "20030909" or @rlad< "20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:59
S104	63	S103 and ((high adj2 ("k" or dielectric)) with metal\$4)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 12:47
S105	0	"10803275"	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:10

S106	2	"6803275"	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:14
S107	3	"6455890"	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:14
S108	3	("6153470" "6320784" "6344403").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/07/11 13:14
S109	12	("4329706" "4354309" "4829024" "5093700" "5298447" "5350698" "5393687" "5481128" "5597745" "5710454" "5877980" "5977601").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/07/11 13:16
S110	9	("3649884" "4253106" "4688078" "4717943" "4748133" "5229631" "5284786" "5289026" "5331185").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/07/11 13:43
S111	18	("5481128").URPN.	USPAT	OR	ON	2006/07/11 13:44
S112	441	S100 and (("ONO" or (\$3oxide with nitride)) same control\$4)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:57
S113	296	S112 and ((polysilicon with (float\$4 or ((charg\$4 or electron) with (trap\$4 hold \$4 keep\$3)))) same ("ONO" or (\$3oxide with nitride)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:59
S114	250	S113 not (\$89 S101 S104 S106 S107 S108 S109 S110 S111)	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:59
S115	181	S114 and (@ad<"20030909" or @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 13:59
S116	5	("3731163" "4794565" "4888630" "5300799" "5304503").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/07/11 14:25
S117	50	("5619051").URPN.	USPAT	OR	ON	2006/07/11 14:31
S118	1352	257/314.ccls.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/11 14:32
S119	4	((("5429970") or ("6133098") or ("6555865") or ("6709928")).PN.	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/07/12 14:29
S120	7	("5234850" "5453634" "5604367" "5949706" "6001687" "6031264" "6144071").PN.	US-PGRUB; USPAT; USOCR	OR	ON	2006/07/12 14:40
S121	124	(high adj2 ("k" or dielectric)) and (polysilicon near3 (float\$4 or ((charg\$4 or electron) with (trap\$4 hold\$4 keep\$3)))) and (("ONO" or (oxide same nitride)) with control) and (spacer or sidewall or (sidewall))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 17:00

S122	155	((spacer or sidewall or (sidewall)) with (on or above or over or atop) with (high adj2 ("k" or dielectric)))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 17:02
S123	35	S121 and ((spacer or sidewall or (sidewall)) with (oxide and nitride))	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 17:02
S124	27	S123 and (@ad<"20030909" or @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/07/12 17:03
S125	82	((tunnel near2 \$2oxide) with metal\$4) and "ONO" and substrate	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:12
S126	124	(tunnel with \$2oxide with metal\$4) and "ONO" and substrate	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:02
S127	103	S126 and control\$4 and float\$3	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:13
S128	93	S127 and polysilicon	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:14
S129	47	S128 and (metal\$4 near2 \$2oxide)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 12:15
S130	34	S129 and (@ad<"20030909" @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 14:17
S131	58	(S126 not S130) and (@ad<"20030909" @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 15:09

S132	7092	(metal\$4 near3 (tunnel\$4 gate) near3 \$2oxide)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 15:08
S133	5730	(S132 not (S130 S131)) and (@ad<"20030909" @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:10
S134	206	S133 and "ONO" and substrate	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:00
S135	78	S134 and (float\$4 with \$4silicon)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:11
S136	0	S135 and (tunnel with \$2oxide with metal \$4)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:02
S137	10	S135 and (tunnel\$3 with \$2oxide with metal\$4)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:04
S138	68	S135 not S137	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:09
S139	108	(metal\$4 adj3 gate adj2 \$2oxide) and float \$4	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:10
S140	85	(S139 not (S130 S131 S135)) and (@ad<"20030909" @rlad<"20030909")	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:10
S141	0	S140 and "ONO"	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:10

S142	30	S140 and (float\$4 with \$4silicon)	US-PGRUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/03 16:12
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